



Dear customers,

About the change in the name such as "Oki Electric Industry Co. Ltd." and "OKI" in documents to OKI Semiconductor Co., Ltd.

The semiconductor business of Oki Electric Industry Co., Ltd. was succeeded to OKI Semiconductor Co., Ltd. on October 1, 2008. Therefore, please accept that although the terms and marks of "Oki Electric Industry Co., Ltd.", "Oki Electric", and "OKI" remain in the documents, they all have been changed to "OKI Semiconductor Co., Ltd.". It is a change of the company name, the company trademark, and the logo, etc. , and NOT a content change in documents.

October 1, 2008
OKI Semiconductor Co., Ltd.

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OKI Semiconductor

MSM514102D/DL

4,194,304-Word × 1-Bit DYNAMIC RAM : STATIC COLUMN MODE TYPE

DESCRIPTION

The MSM514102D/DL is a 4,194,304-word × 1-bit dynamic RAM fabricated in Oki's silicon-gate CMOS technology. The MSM514102D/DL achieves high integration, high-speed operation, and low-power consumption because Oki manufactures the device in a quadruple-layer polysilicon/single-layer metal CMOS process. The MSM514102D/DL is available in a 26/20-pin plastic SOJ, 20-pin plastic ZIP, or 26/20-pin plastic TSOP. The MSM514102DL (the low-power version) is specially designed for lower-power applications.

FEATURES

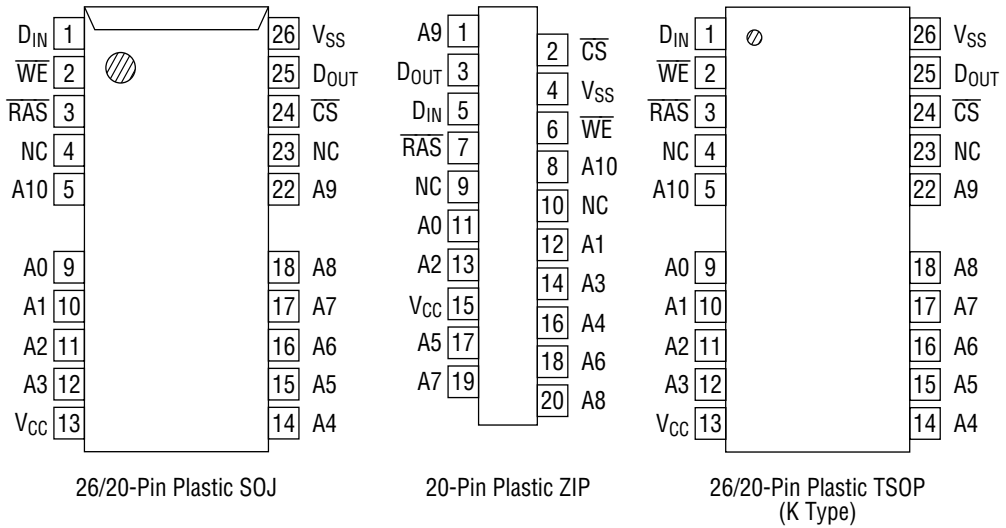
- 4,194,304-word × 1-bit configuration
 - Single 5 V power supply, ±10% tolerance
 - Input : TTL compatible, low input capacitance
 - Output : TTL compatible, 3-state
 - Refresh : 1024 cycles/16 ms, 1024 cycles/128 ms (L-version)
 - Static Column mode, read modify write capability
 - \overline{CS} before \overline{RAS} refresh, hidden refresh, \overline{RAS} -only refresh capability
 - Multi-bit test mode capability
 - Package options:

26/20-pin 300 mil plastic SOJ	(SOJ26/20-P-300-1.27)	(Product : MSM514102D/DL-xxSJ)
20-pin 400 mil plastic ZIP	(ZIP20-P-400-1.27)	(Product : MSM514102D/DL-xxZS)
26/20-pin 300 mil plastic TSOP	(TSOPII26/20-P-300-1.27-K)	(Product : MSM514102D/DL-xxTS-K)
- xx indicates speed rank.

PRODUCT FAMILY

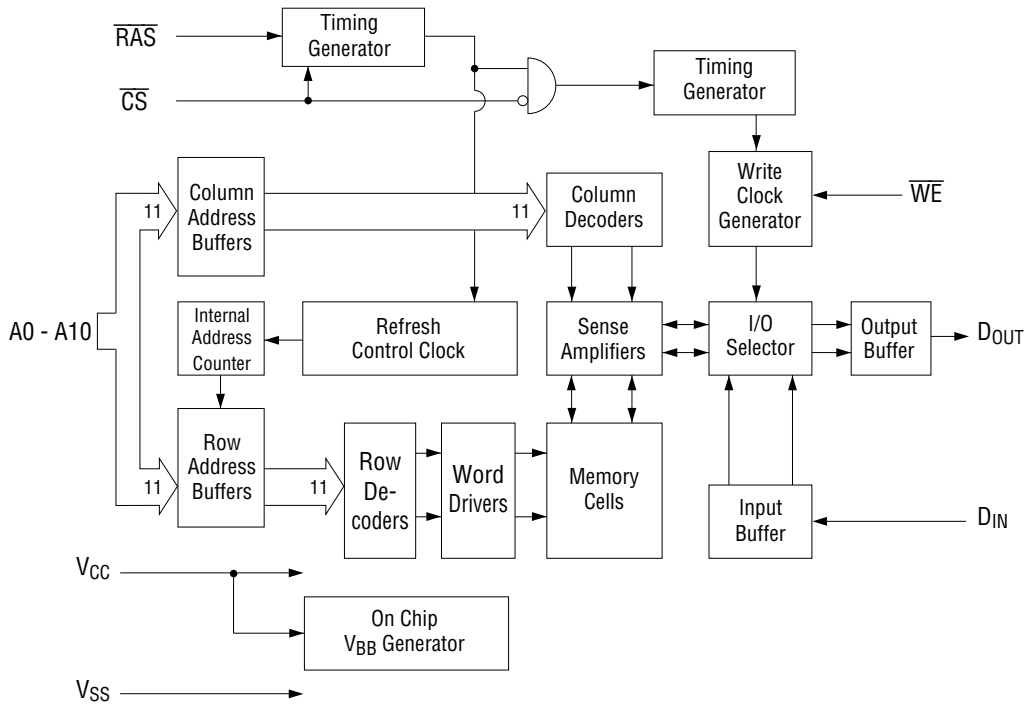
Family	Access Time (Max.)			Cycle Time (Min.)	Power Dissipation	
	t _{RAC}	t _{AA}	t _{CAC}		Operating (Max.)	Standby (Max.)
MSM514102D/DL-60	60 ns	30 ns	15 ns	110 ns	495 mW	5.5 mW/ 1.1 mW (L-version)
MSM514102D/DL-70	70 ns	35 ns	20 ns	130 ns	440 mW	
MSM514102D/DL-80	80 ns	40 ns	20 ns	150 ns	385 mW	

PIN CONFIGURATION (TOP VIEW)



Pin Name	Function
A0 - A10	Address Input
RAS	Row Address Strobe
CS	Chip Select Input
D _{IN}	Data Input
D _{OUT}	Data Output
WE	Write Enable
V _{CC}	Power Supply (5 V)
V _{SS}	Ground (0 V)
NC	No Connection

BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Voltage on Any Pin Relative to V_{SS}	V_T	-1.0 to 7.0	V
Short Circuit Output Current	I_{OS}	50	mA
Power Dissipation	P_D^*	1	W
Operating Temperature	T_{opr}	0 to 70	°C
Storage Temperature	T_{stg}	-55 to 150	°C

*: $T_a = 25^\circ\text{C}$

Recommended Operating Conditions

($T_a = 0^\circ\text{C}$ to 70°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Power Supply Voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input High Voltage	V_{IH}	2.4	—	6.5	V
Input Low Voltage	V_{IL}	-1.0	—	0.8	V

Capacitance

($V_{CC} = 5\text{ V} \pm 10\%$, $T_a = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

Parameter	Symbol	Typ.	Max.	Unit
Input Capacitance ($A_0 - A_{10}, D_{IN}$)	C_{IN1}	—	6	pF
Input Capacitance ($\overline{RAS}, \overline{CS}, \overline{WE}$)	C_{IN2}	—	7	pF
Output Capacitance (D_{OUT})	C_{OUT}	—	7	pF

DC Characteristics

(V_{CC} = 5 V ±10%, T_a = 0°C to 70°C)

Parameter	Symbol	Condition	MSM514102 D/DL-60		MSM514102 D/DL-70		MSM514102 D/DL-80		Unit	Note
			Min.	Max.	Min.	Max.	Min.	Max.		
Output High Voltage	V _{OH}	I _{OH} = -5.0 mA	2.4	V _{CC}	2.4	V _{CC}	2.4	V _{CC}	V	
Output Low Voltage	V _{OL}	I _{OL} = 4.2 mA	0	0.4	0	0.4	0	0.4	V	
Input Leakage Current	I _{LI}	0 V ≤ V _I ≤ 6.5 V; All other pins not under test = 0 V	-10	10	-10	10	-10	10	μA	
Output Leakage Current	I _{LO}	D _{OUT} disable 0 V ≤ V _O ≤ 5.5 V	-10	10	-10	10	-10	10	μA	
Average Power Supply Current (Operating)	I _{CC1}	$\overline{\text{RAS}}$, $\overline{\text{CS}}$ cycling, t _{RC} = Min.	—	90	—	80	—	70	mA	1, 2
Power Supply Current (Standby)	I _{CC2}	$\overline{\text{RAS}}$, $\overline{\text{CS}} = V_{IH}$	—	2	—	2	—	2	mA	1
		$\overline{\text{RAS}}$, $\overline{\text{CS}}$ ≥ V _{CC} - 0.2 V	—	1	—	1	—	1		
Power Supply Current (Standby)	I _{CC5}	≥ V _{CC} - 0.2 V	—	200	—	200	—	200	μA	1, 5
		$\overline{\text{RAS}} = V_{IH}$, $\overline{\text{CS}} = V_{IL}$, D _{OUT} = enable	—	5	—	5	—	5		
Average Power Supply Current (RAS-only Refresh)	I _{CC3}	$\overline{\text{RAS}}$ cycling, $\overline{\text{CS}} = V_{IH}$, t _{RC} = Min.	—	90	—	80	—	70	mA	1, 2
Average Power Supply Current (CS before RAS Refresh)	I _{CC6}	$\overline{\text{RAS}}$ cycling, $\overline{\text{CS}}$ before $\overline{\text{RAS}}$	—	90	—	80	—	70	mA	1, 2
Average Power Supply Current (Static Column Mode)	I _{CC9}	$\overline{\text{RAS}} = V_{IL}$, Address cycling, t _{SC} = Min.	—	80	—	70	—	60	mA	1, 3
Average Power Supply Current (Battery Backup)	I _{CC10}	t _{RC} = 125 μs, $\overline{\text{CS}}$ before $\overline{\text{RAS}}$, t _{RAS} ≤ 1 μs	—	300	—	300	—	300	μA	1, 4, 5

- Notes :
1. I_{CC} Max. is specified as I_{CC} for output open condition.
 2. The address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$.
 3. The address can be changed once or less while $\overline{\text{CS}} = V_{IH}$.
 4. V_{CC} - 0.2 V ≤ V_{IH} ≤ 6.5 V, -1.0 V ≤ V_{IL} ≤ 0.2 V.
 5. L-version.

AC Characteristics (1/2)

(V_{CC} = 5 V ±10%, T_a = 0°C to 70°C) Note 1, 2, 3, 12, 13

Parameter	Symbol	MSM514102 D/DL-60		MSM514102 D/DL-70		MSM514102 D/DL-80		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.		
Random Read or Write Cycle Time	t _{RC}	110	—	130	—	150	—	ns	
Read Modify Write Cycle Time	t _{RWC}	130	—	155	—	175	—	ns	
Static Column Mode Cycle Time	t _{SC}	35	—	40	—	45	—	ns	
Static Column Mode Read Modify Write Cycle Time	t _{SRWC}	60	—	70	—	80	—	ns	
Access Time from $\overline{\text{RAS}}$	t _{RAC}	—	60	—	70	—	80	ns	4, 5, 6
Access Time from $\overline{\text{CS}}$	t _{CAC}	—	15	—	20	—	20	ns	4, 5
Access Time from Column Address	t _{AA}	—	30	—	35	—	40	ns	4, 6, 7
Access Time from Last Write	t _{ALW}	—	55	—	65	—	75	ns	4, 7
Output Enable Time referenced to $\overline{\text{WE}}$	t _{OW}	—	15	—	20	—	20	ns	4
Output Low Impedance Time from $\overline{\text{CS}}$	t _{CLZ}	0	—	0	—	0	—	ns	4
Data Output Hold Time referenced to Column Address	t _{AOH}	5	—	5	—	5	—	ns	
Data Output Hold Time from $\overline{\text{WE}}$	t _{WOH}	0	—	0	—	0	—	ns	
$\overline{\text{CS}}$ to Data Output Buffer Turn-off Delay Time	t _{OFF}	0	15	0	20	0	20	ns	8
Transition Time	t _T	3	50	3	50	3	50	ns	3
Refresh Period	t _{REF}	—	16	—	16	—	16	ms	
Refresh Period (L-version)	t _{REF}	—	128	—	128	—	128	ms	
$\overline{\text{RAS}}$ Precharge Time	t _{RP}	40	—	50	—	60	—	ns	
$\overline{\text{RAS}}$ Pulse Width	t _{RAS}	60	10,000	70	10,000	80	10,000	ns	
$\overline{\text{RAS}}$ Pulse Width (Static Column Mode)	t _{RASC}	60	100,000	70	100,000	80	100,000	ns	
$\overline{\text{RAS}}$ Hold Time	t _{RSH}	15	—	20	—	20	—	ns	
$\overline{\text{CS}}$ Precharge Time (Static Column Mode)	t _{CP}	10	—	10	—	10	—	ns	
$\overline{\text{CS}}$ Pulse Width	t _{CS}	15	10,000	20	10,000	20	10,000	ns	
$\overline{\text{CS}}$ Hold Time	t _{CSH}	60	—	70	—	80	—	ns	
$\overline{\text{CS}}$ to $\overline{\text{RAS}}$ Precharge Time	t _{CRP}	5	—	5	—	5	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{CS}}$ Delay Time	t _{RCD}	20	45	20	50	20	60	ns	5
$\overline{\text{RAS}}$ to Column Address Delay Time	t _{RAD}	15	30	15	35	15	40	ns	6
Row Address Set-up Time	t _{ASR}	0	—	0	—	0	—	ns	
Row Address Hold Time	t _{RAH}	10	—	10	—	10	—	ns	
Column Address Set-up Time	t _{ASC}	0	—	0	—	0	—	ns	
Column Address Hold Time	t _{CAH}	15	—	15	—	15	—	ns	
Column Address Hold Time from $\overline{\text{RAS}}$ (Write Cycle)	t _{AWR}	50	—	55	—	60	—	ns	
Column Address Hold Time from $\overline{\text{RAS}}$	t _{AR}	75	—	85	—	95	—	ns	
Column Address to $\overline{\text{RAS}}$ Lead Time	t _{RAL}	30	—	35	—	40	—	ns	
Column Address Hold Time from $\overline{\text{RAS}}$ Precharge	t _{AH}	10	—	10	—	10	—	ns	

AC Characteristics (2/2)

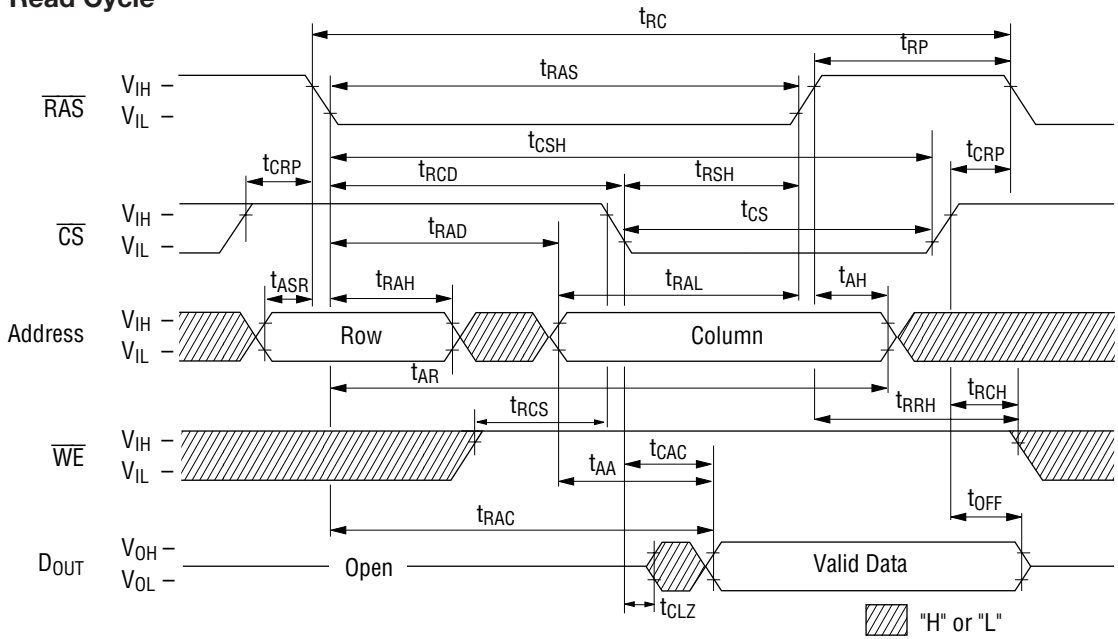
(V_{CC} = 5 V ±10%, T_a = 0°C to 70°C) Note 1, 2, 3, 12, 13

Parameter	Symbol	MSM514102 D/DL-60		MSM514102 D/DL-70		MSM514102 D/DL-80		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.		
Column Address Hold Time	t _{AHLW}	55	—	65	—	75	—	ns	
Last Write to Column Address Delay Time	t _{LWAD}	20	25	20	30	20	35	ns	7
Read Command Set-up Time	t _{RCS}	0	—	0	—	0	—	ns	
Read Command Hold Time	t _{RCH}	0	—	0	—	0	—	ns	9
Read Command Hold Time referenced to $\overline{\text{RAS}}$	t _{RRH}	0	—	0	—	0	—	ns	9
Write Command Set-up Time	t _{WCS}	0	—	0	—	0	—	ns	10
Write Command Hold Time	t _{WCH}	10	—	10	—	15	—	ns	
Write Command Hold Time from $\overline{\text{RAS}}$	t _{WCR}	45	—	50	—	60	—	ns	
Write Command Pulse Width	t _{WP}	10	—	10	—	15	—	ns	
Write Invalid Time	t _{WI}	10	—	10	—	10	—	ns	
Write Command Hold Time (D _{OUT} Disable)	t _{WH}	0	—	0	—	0	—	ns	10
Write Command to $\overline{\text{RAS}}$ Lead Time	t _{RWL}	15	—	20	—	20	—	ns	
Write Command to $\overline{\text{CS}}$ Lead Time	t _{CWL}	15	—	20	—	20	—	ns	
Data-in Set-up Time	t _{DS}	0	—	0	—	0	—	ns	11
Data-in Hold Time	t _{DH}	15	—	15	—	15	—	ns	11
Data-in Hold Time from $\overline{\text{RAS}}$	t _{DHR}	50	—	55	—	60	—	ns	
$\overline{\text{CS}}$ to $\overline{\text{WE}}$ Delay Time	t _{CWD}	15	—	20	—	20	—	ns	10
Column Address to $\overline{\text{WE}}$ Delay Time	t _{AWD}	30	—	35	—	40	—	ns	10
$\overline{\text{RAS}}$ to $\overline{\text{WE}}$ Delay Time	t _{RWD}	60	—	70	—	80	—	ns	10
$\overline{\text{CS}}$ Active Delay Time from $\overline{\text{RAS}}$ Precharge	t _{RPC}	10	—	10	—	10	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{CS}}$ Set-up Time ($\overline{\text{CS}}$ before $\overline{\text{RAS}}$)	t _{CSR}	5	—	5	—	5	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{CS}}$ Hold Time ($\overline{\text{CS}}$ before $\overline{\text{RAS}}$)	t _{CHR}	10	—	10	—	10	—	ns	
$\overline{\text{WE}}$ to $\overline{\text{RAS}}$ Precharge Time ($\overline{\text{CS}}$ before $\overline{\text{RAS}}$)	t _{WRP}	10	—	10	—	10	—	ns	
$\overline{\text{WE}}$ Hold Time from $\overline{\text{RAS}}$ ($\overline{\text{CS}}$ before $\overline{\text{RAS}}$)	t _{WRH}	10	—	10	—	10	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{WE}}$ Set-up Time (Test Mode)	t _{WTS}	10	—	10	—	10	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{WE}}$ Hold Time (Test Mode)	t _{WTH}	10	—	10	—	10	—	ns	

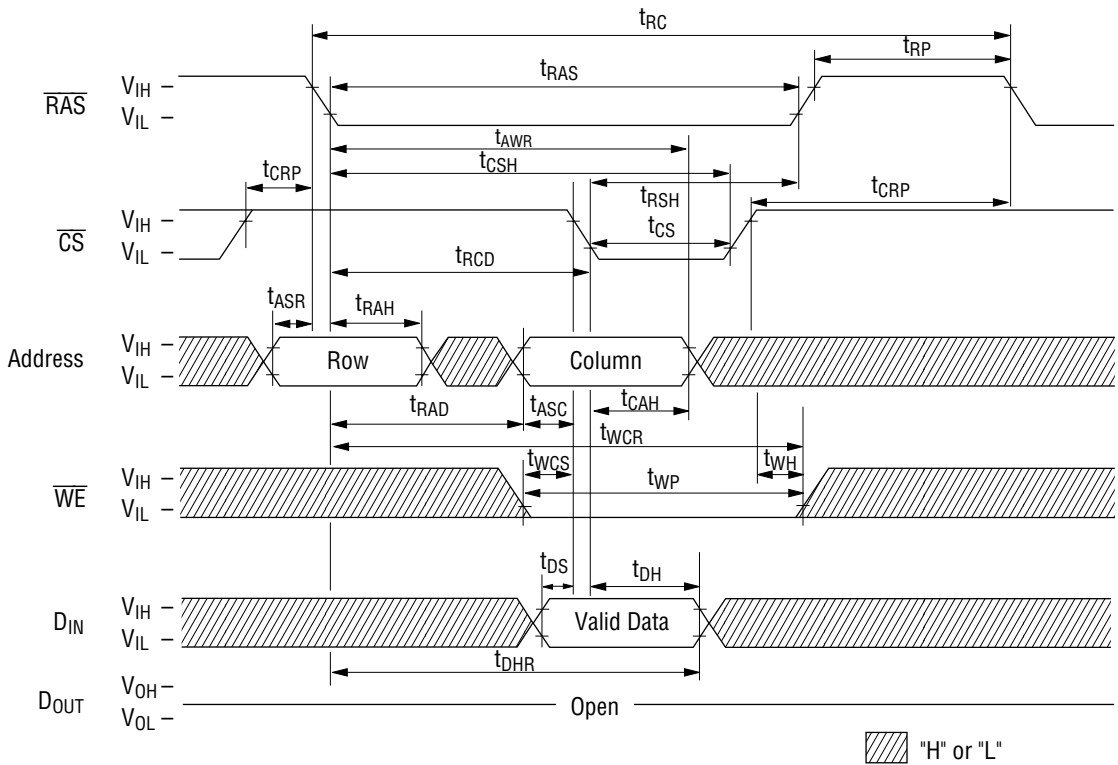
- Notes:
1. A start-up delay of 200 μ s is required after power-up, followed by a minimum of eight initialization cycles ($\overline{\text{RAS}}$ -only refresh or $\overline{\text{CS}}$ before $\overline{\text{RAS}}$ refresh) before proper device operation is achieved.
 2. The AC characteristics assume $t_T = 5$ ns.
 3. V_{IH} (Min.) and V_{IL} (Max.) are reference levels for measuring input timing signals. Transition times (t_T) are measured between V_{IH} and V_{IL} .
 4. This parameter is measured with a load circuit equivalent to 2 TTL loads and 100 pF.
 5. Operation within the t_{RCD} (Max.) limit ensures that t_{RAC} (Max.) can be met. t_{RCD} (Max.) is specified as a reference point only. If t_{RCD} is greater than the specified t_{RCD} (Max.) limit, then the access time is controlled by t_{CAC} .
 6. Operation within the t_{RAD} (Max.) limit ensures that t_{RAC} (Max.) can be met. t_{RAD} (Max.) is specified as a reference point only. If t_{RAD} is greater than the specified t_{RAD} (Max.) limit, then the access time is controlled by t_{AA} .
 7. Operating within the t_{LWAD} (Max.) limit ensures that t_{ALW} (Max.) can be met. t_{LWAD} (Max.) is specified as a reference point only. If t_{LWAD} is greater than the specified t_{LWAD} (Max.) limit, then the access time is controlled by t_{AA} .
 8. t_{OFF} (Max.) defines the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
 9. t_{RCH} or t_{RRH} must be satisfied for a read cycle.
 10. t_{WCS} , t_{CWD} , t_{RWD} and t_{AWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}$ (Min.), then the cycle is an early write cycle and the data out will remain open circuit (high impedance) throughout the entire cycle. If $t_{CWD} \geq t_{CWD}$ (Min.), $t_{RWD} \geq t_{RWD}$ (Min.) and $t_{AWD} \geq t_{AWD}$ (Min.), then the cycle is a read modify write cycle and data out will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, then the condition of the data out (at access time) is indeterminate.
 11. These parameters are referenced to the $\overline{\text{CS}}$ leading edge in an early write cycle, and to the $\overline{\text{WE}}$ leading edge in a read modify write cycle.
 12. The test mode is initiated by performing a $\overline{\text{WE}}$ and $\overline{\text{CS}}$ before $\overline{\text{RAS}}$ refresh cycle. This mode is latched and remains in effect until the exit cycle is generated. The test mode specified in this data sheet is an 8-bit parallel test function. RA10, CA10 and CA0 are not used. In a read cycle, if all internal bits are equal, the data output pin will indicate a high level. If any internal bits are not equal, the data output pin will indicate a low level. The test mode is cleared and the memory device returned to its normal operating state by performing a $\overline{\text{RAS}}$ -only refresh cycle or a $\overline{\text{CS}}$ before $\overline{\text{RAS}}$ refresh cycle.
 13. In a test mode read cycle, the value of access time parameters is delayed for 5 ns for the specified value. These parameters should be specified in test mode cycle by adding the above value to the specified value in this data sheet.

TIMING WAVEFORM

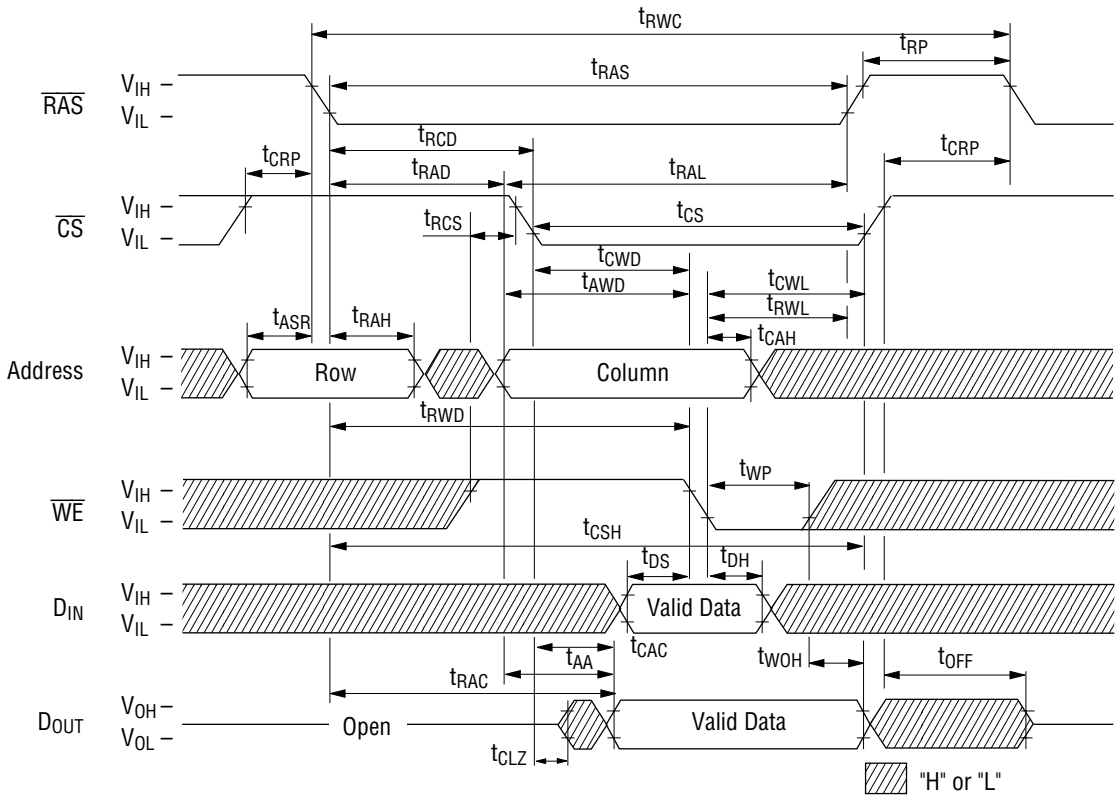
Read Cycle



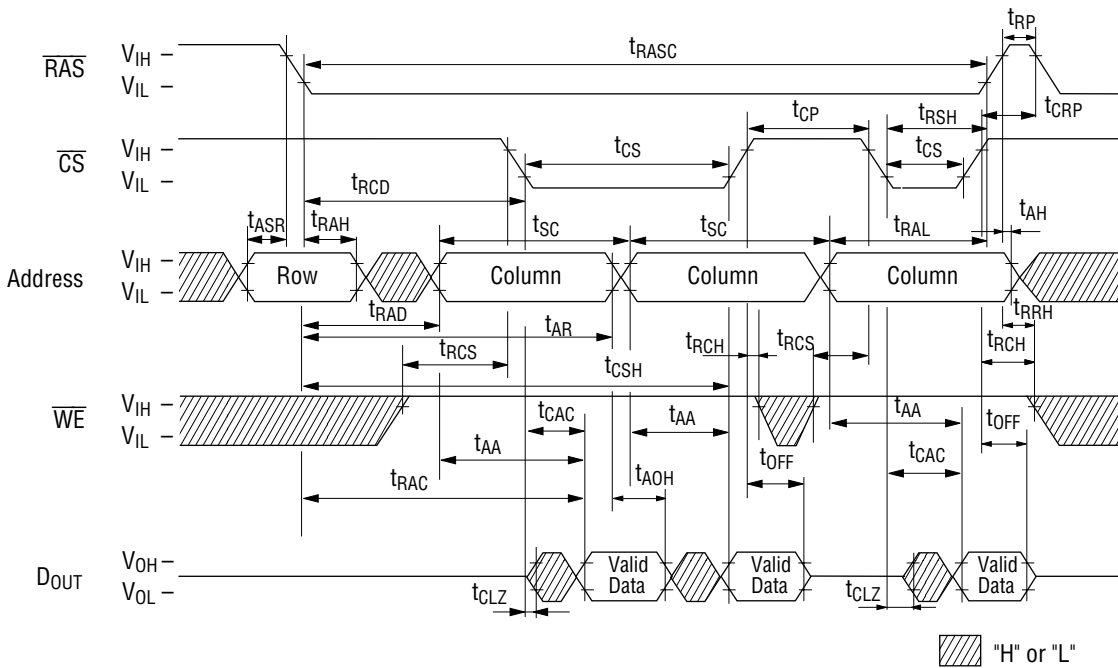
Write Cycle (Early Write)



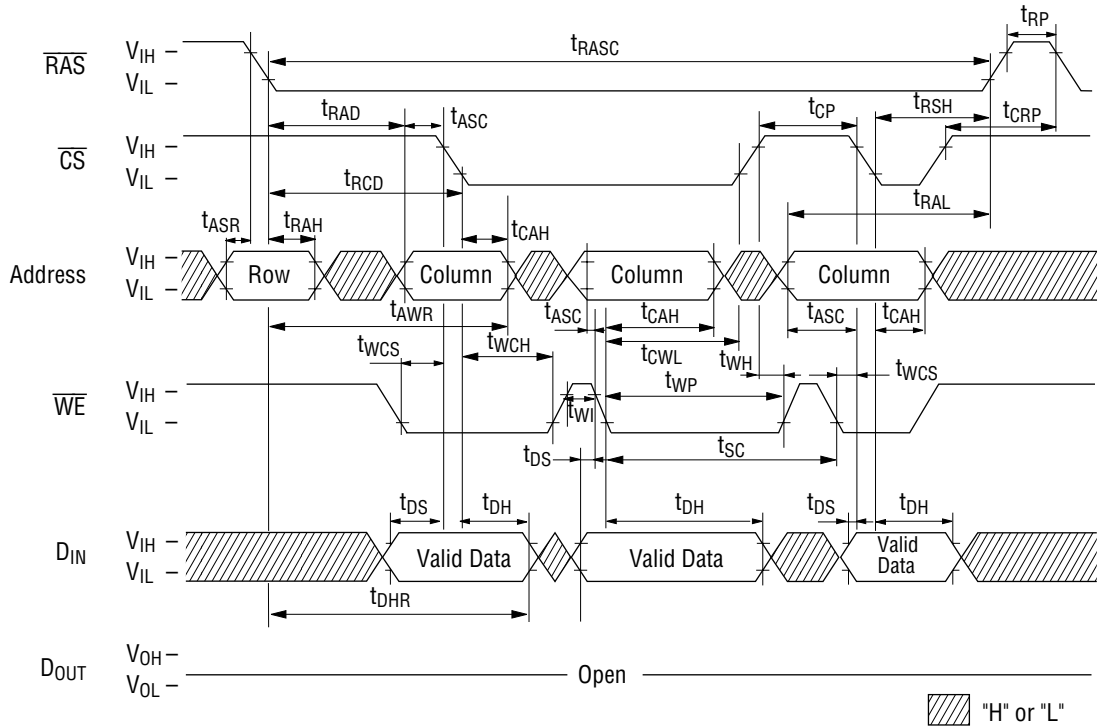
Read Modify Write Cycle



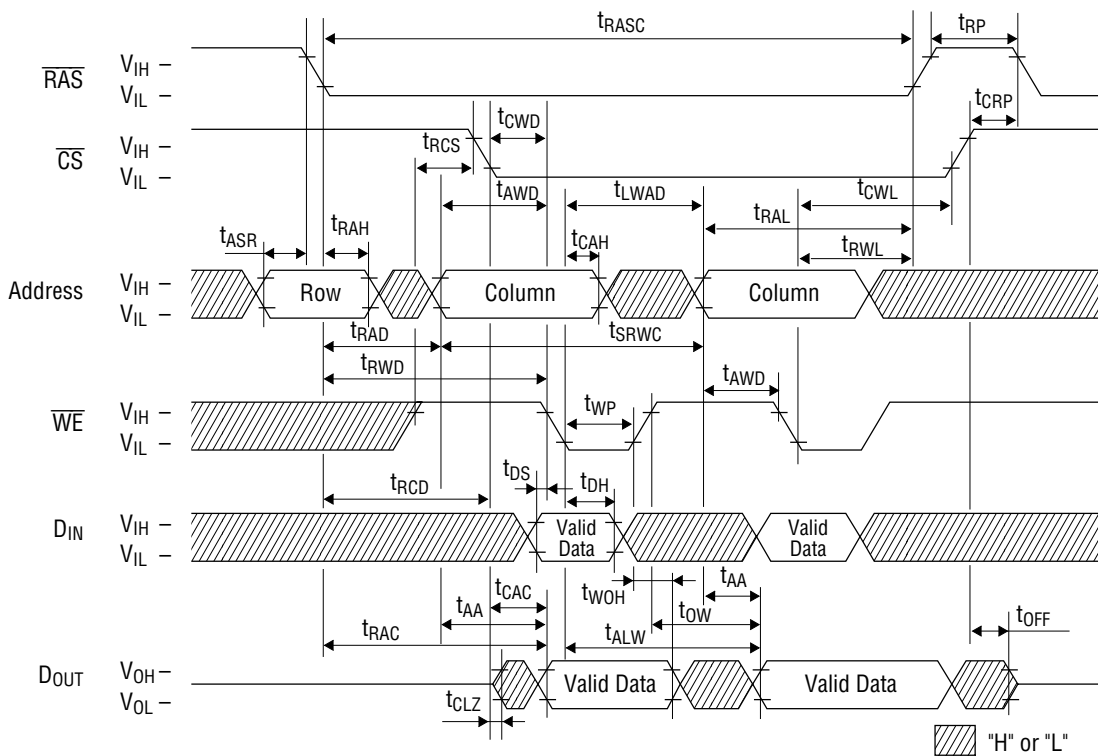
Static Column Mode Read Cycle



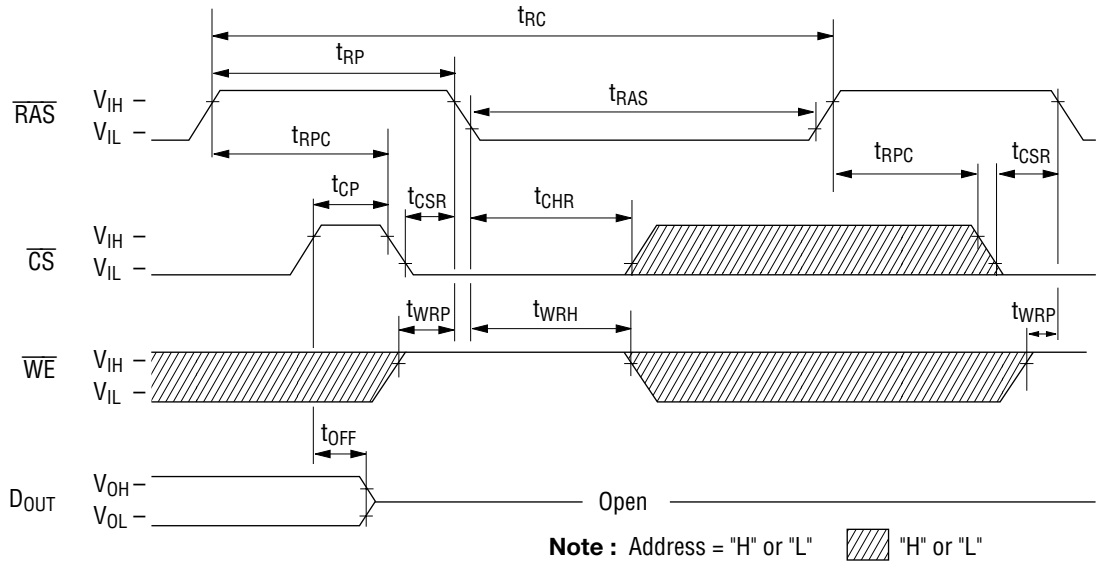
Static Column Mode Write Cycle (Early Write)



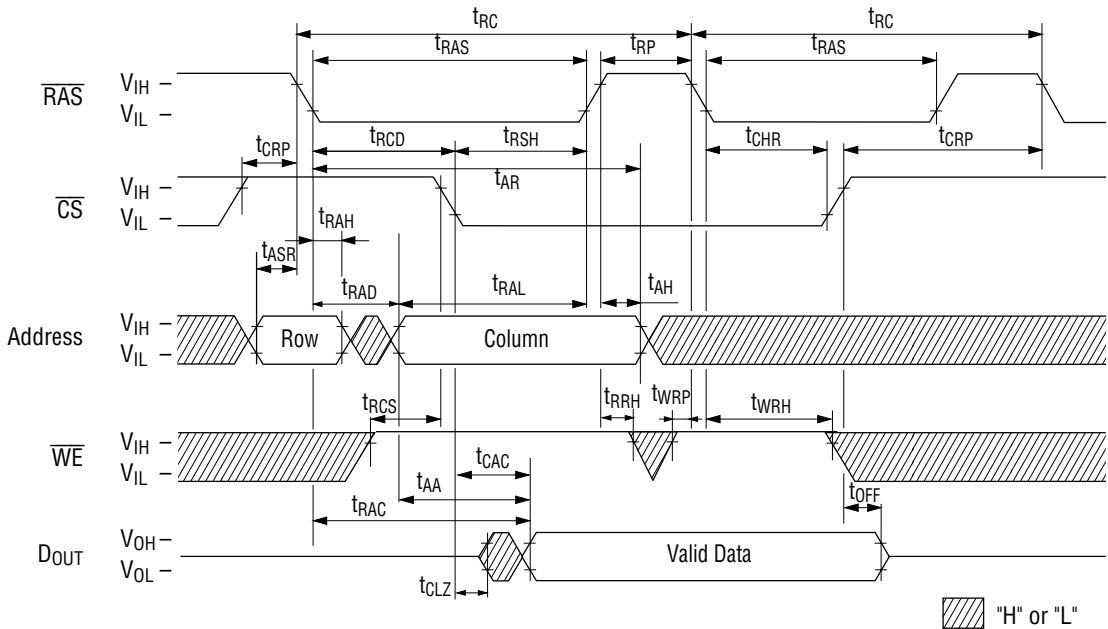
Static Column Mode Read Modify Write Cycle



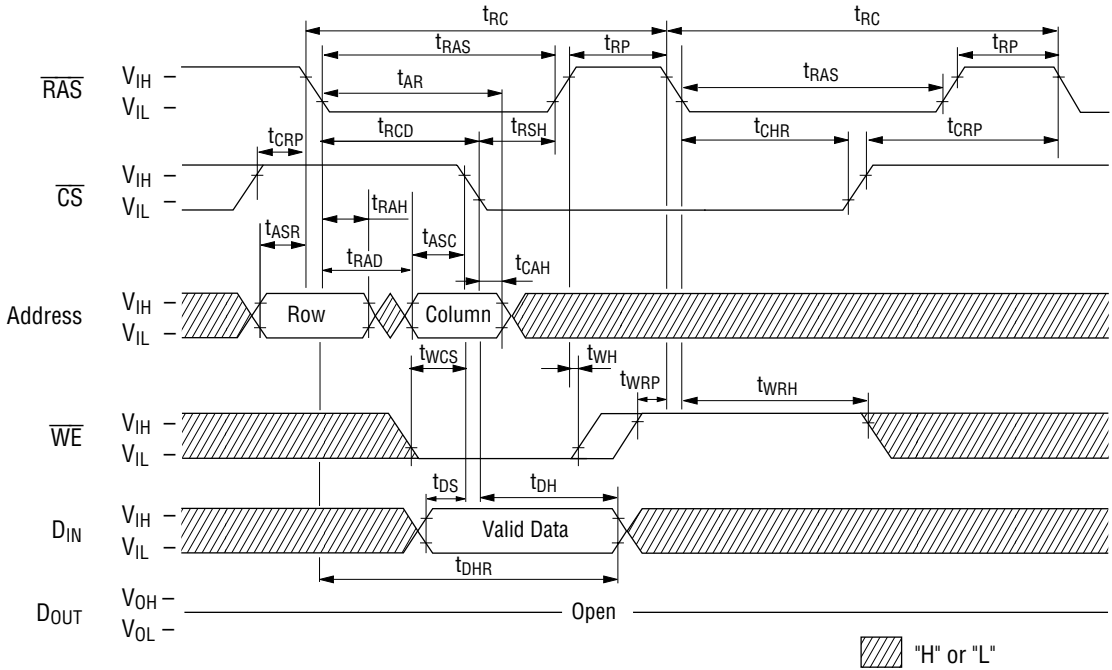
CS before RAS Refresh Cycle



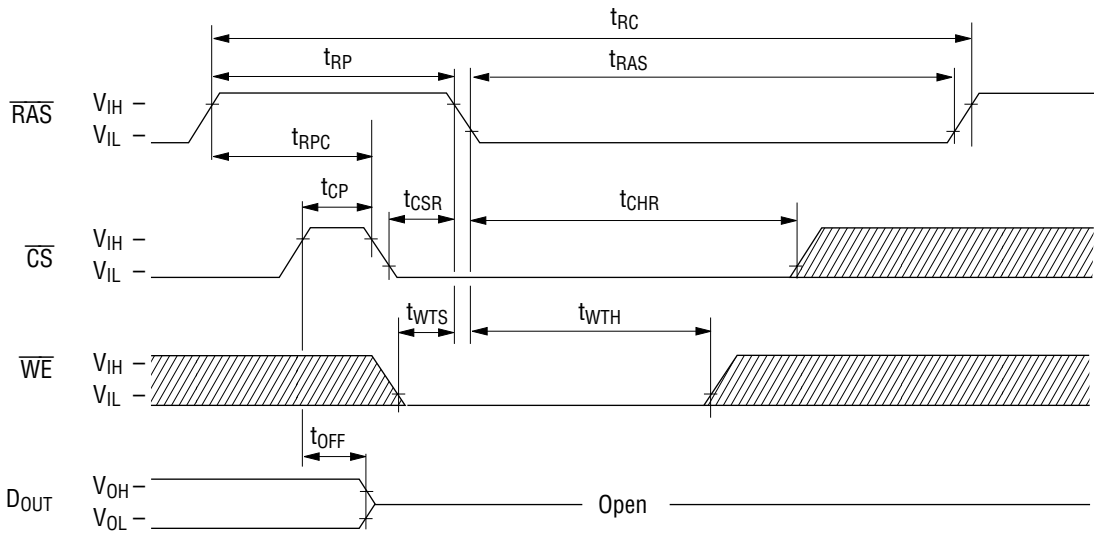
Hidden Refresh Read Cycle



Hidden Refresh Write Cycle



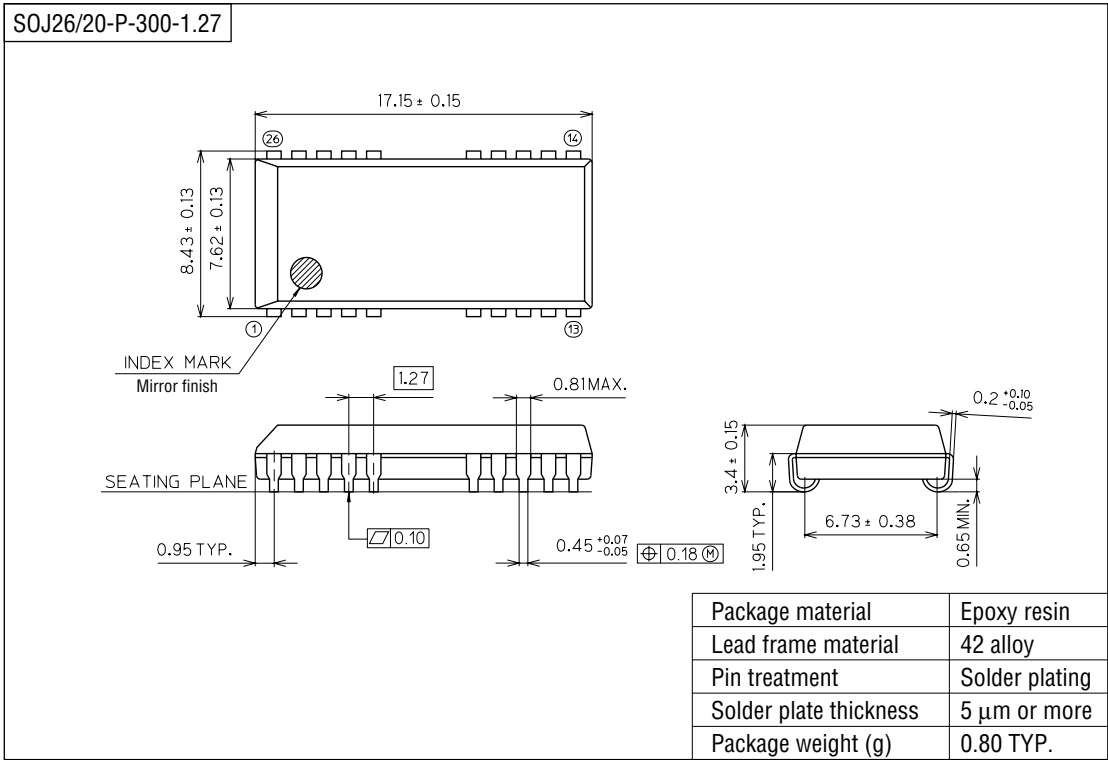
Test Mode Initiate Cycle



Note: Address, D_{IN} = "H" or "L" "H" or "L"

PACKAGE DIMENSIONS

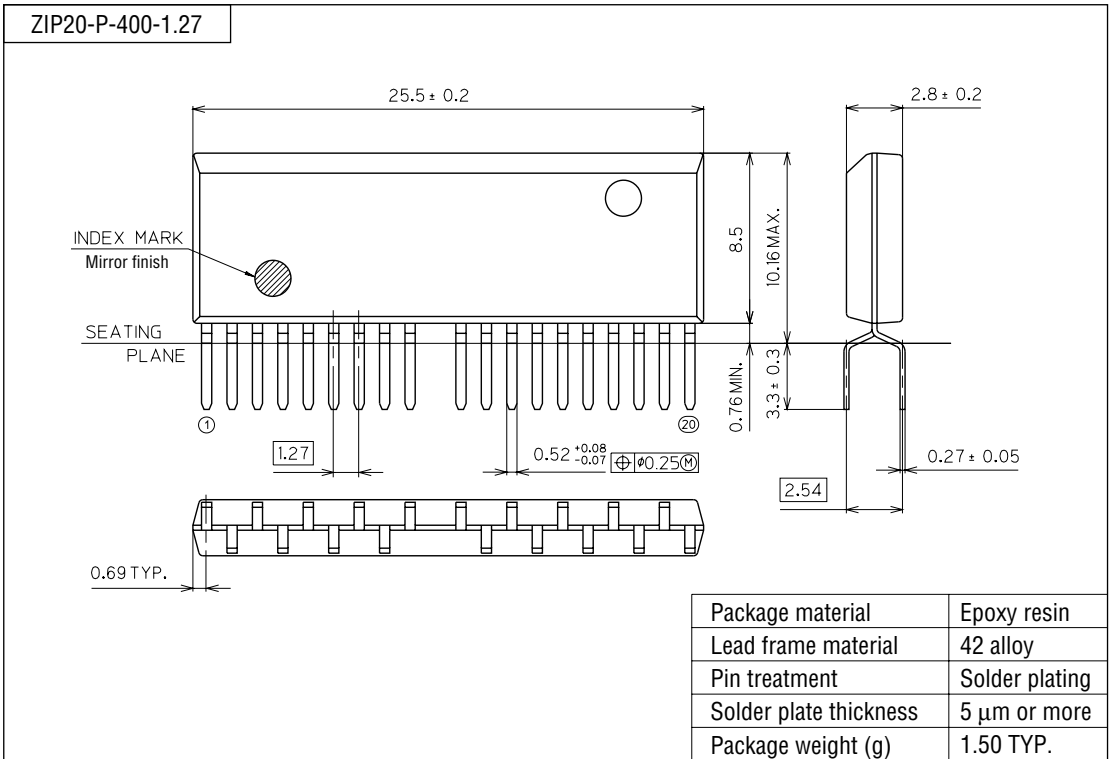
(Unit : mm)



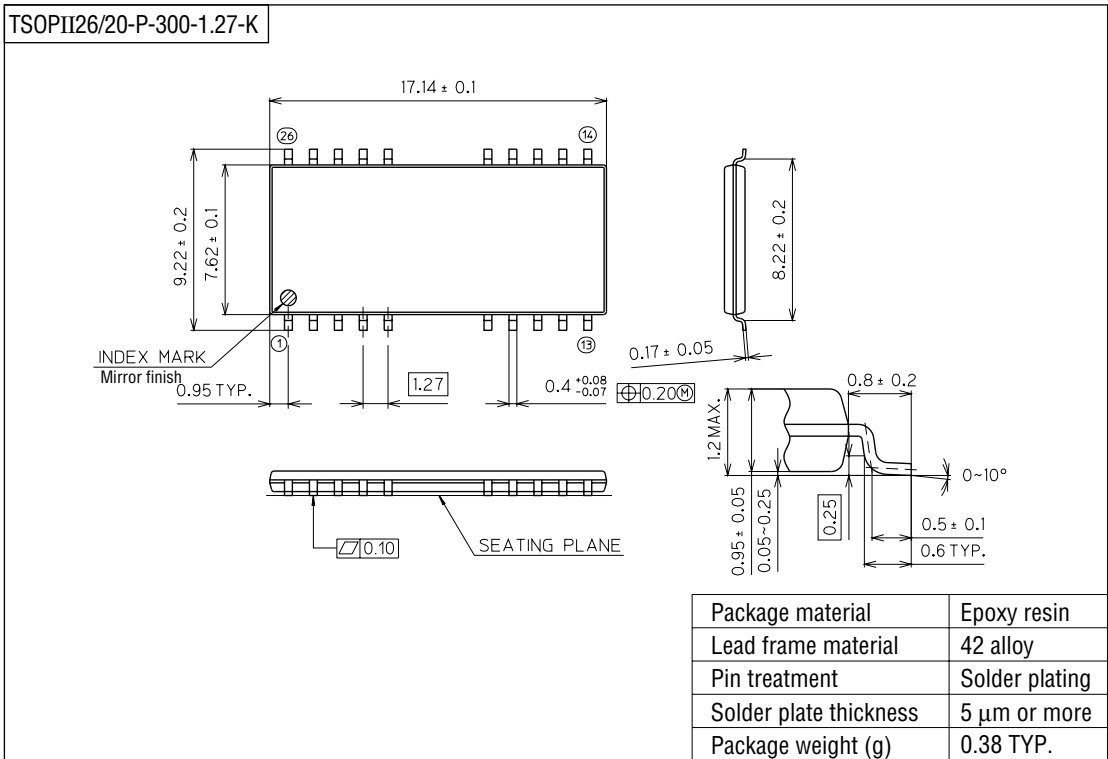
Notes for Mounting the Surface Mount Type Package

The SOP, QFP, TSOP, TQFP, LQFP, SOJ, QFJ (PLCC), SHP, and BGA are surface mount type packages, which are very susceptible to heat in reflow mounting and humidity absorbed in storage. Therefore, before you perform reflow mounting, contact Oki's responsible sales person on the product name, package name, pin number, package code and desired mounting conditions (reflow method, temperature and times).

(Unit : mm)



(Unit : mm)



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NOTICE

1. The information contained herein can change without notice owing to product and/or technical improvements. Before using the product, please make sure that the information being referred to is up-to-date.
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